

SuperMOS – SOT-23 -20V BV_{DSS} , 30m Ω $R_{DS(on)}$, P-channel MOSFET

1. Description

The DMG3415U-7(ES) is P-Channel enhancement MOS Field Effect Transistor. Uses advanced trench technology and design to provide excellent $R_{DS(on)}$ with low gate charge. Device is suitable for use in DC-DC conversion, power switch and charging circuit. Standard Product DMG3415U-7(ES) is Pb-free.

2. Features

- -20V, $R_{DS(on)}$ =30m Ω (Typ.) @ V_{GS} =-4.5V
 $R_{DS(on)}$ =36m Ω (Typ.) @ V_{GS} =-2.5V
- Fast Switching
- High density cell design for low $R_{DS(on)}$
- Material: Halogen free
- Reliable and rugged
- Avalanche Rated
- Low leakage current

3. Applications

- PWM applications
- Load switch
- Power management in portable/desktop PCs
- DC/DC conversion

4. Ordering Information

Part Number	Package	Marking	Material	Packing	Quantity per reel	Flammability Rating	Reel Size
DMG3415U-7(ES)	SOT-23	R15	Halogen free	Tape & Reel	3,000 PCS	UL 94V-0	7 inches

Table-1 Ordering information

5. Pin Configuration and Functions

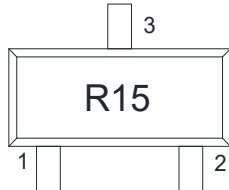
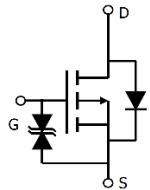
Pin	Function	Outline	Circuit Diagram
1	Gate		
2	Source		
3	Drain		

Table-2 Pin configuration

6. Specification

Absolute Maximum Rating & Thermal Characteristics

Ratings at 25 °C ambient temperature unless otherwise specified.

Parameter		Symbol	Limit	Unit
Drain-Source Voltage		BV_{DSS}	-20	V
Gate-Source Voltage		V_{GS}	± 10	V
Continuous Drain Current	$T_A=25^{\circ}\text{C}$	I_D	-4.9	A
	$T_A=75^{\circ}\text{C}$		-3.8	
Maximum Power Dissipation	$T_A=25^{\circ}\text{C}$	P_D	1.39	W
	$T_A=75^{\circ}\text{C}$		0.83	
Pulsed Drain Current		I_{DM}	-15.6	A
Operating Junction Temperature		T_J	150	$^{\circ}\text{C}$
Storage Temperature Range		T_{stg}	-55 to +150	$^{\circ}\text{C}$

Thermal resistance ratings

Single Operation				
Parameter	Symbol	Typical	Maximum	Unit
Junction-to-Ambient Thermal Resistance ($t \leq 10\text{s}$)	$R_{\theta JA}$	65	90	$^{\circ}\text{C/W}$
Junction-to-Lead Thermal Resistance	$R_{\theta JL}$	43	52	

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Electrical Characteristics

At TA = 25°C unless otherwise specified

Parameter	Symbol	Test Conditions	Min.	Typ.	Max.	Unit
OFF CHARACTERISTICS						
Drain-to-Source Breakdown Voltage	BV _{DSS}	V _{GS} =0V, I _D =-250uA	-20			V
Zero Gate Voltage Drain Current	I _{DSS}	V _{GS} =0V, V _{DS} =-20V			-1	uA
Gate-to-source Leakage Current	I _{GSS}	V _{GS} =±10V, V _{DS} =0V			±10	uA
ON CHARACTERISTICS						
Gate Threshold Voltage	V _{GS(TH)}	V _{GS} =V _{DS} , I _D =-250uA	-0.5	-0.7	-0.9	V
Drain-to-source On-resistance	R _{DS(on)}	V _{GS} =-4.5V, I _D =-4A		30	37	mΩ
		V _{GS} =-2.5V, I _D =-4A		36	47	
Forward Transconductance	g _{FS}	V _{DS} =-5V, I _D =-4A			40	S
CHARGES, CAPACITANCES AND GATE RESISTANCE						
Input Capacitance	C _{ISS}	V _{GS} =0V, V _{DS} =-10V f=1MHz		750		pF
Output Capacitance	C _{OSS}			115		
Reverse Transfer Capacitance	C _{RSS}			80		
Total Gate Charge	Q _{G(TOT)}	V _{GS} =-4.5V, V _{DS} =-10V I _D =-4A		9.5		nC
Gate-to-Source Charge	Q _{GS}			1		
Gate-to-Drain Charge	Q _{GD}			2.3		
SWITCHING CHARACTERISTICS						
Turn-On Delay Time	t _{d(ON)}	V _{GS} =-4.5V, V _{DS} =-10V R _L =2.5Ω, R _G =3Ω		13		ns
Rise Time	t _r			10		
Turn-Off Delay Time	t _{d(OFF)}			20		
Fall Time	t _f			30		
BODY DIODE CHARACTERISTICS						
Forward Voltage	V _{SD}	V _{GS} =0V, I _{SD} =-1.0A			-1.5	V

7. Typical Characteristic

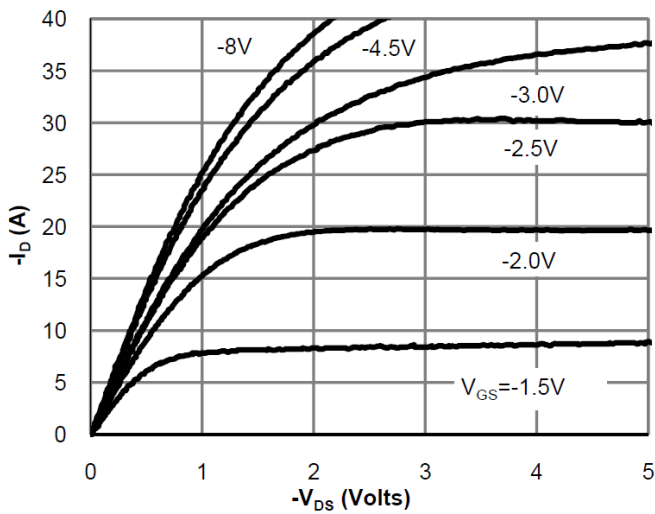


Fig 1: On-Region Characteristics

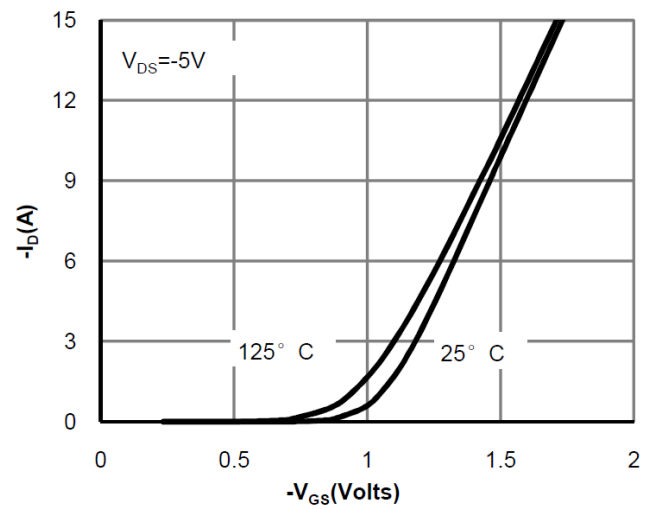


Figure 2: Transfer Characteristics

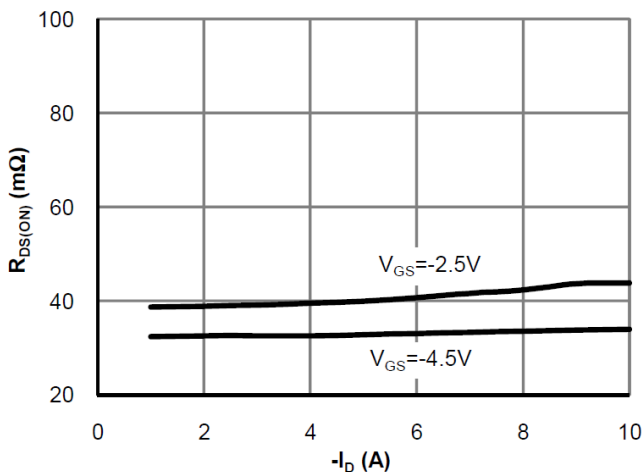


Figure 3: On-Resistance vs. Drain Current and Gate Voltage

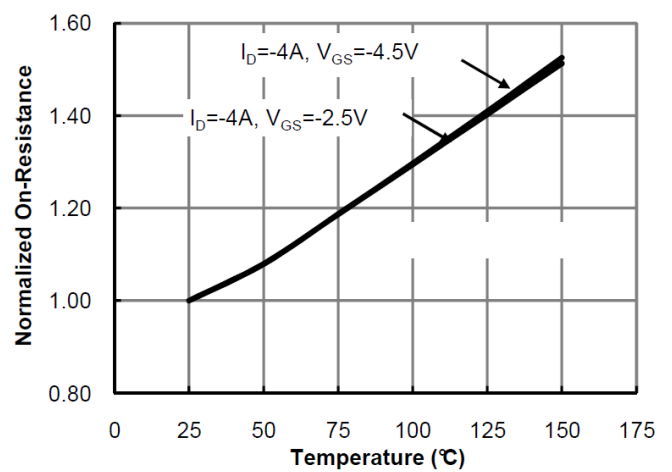


Figure 4: On-Resistance vs. Junction Temperature

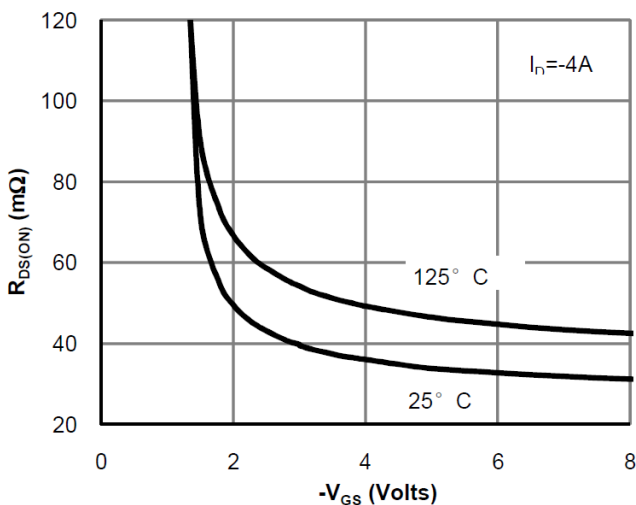


Figure 5: On-Resistance vs. Gate-Source Voltage

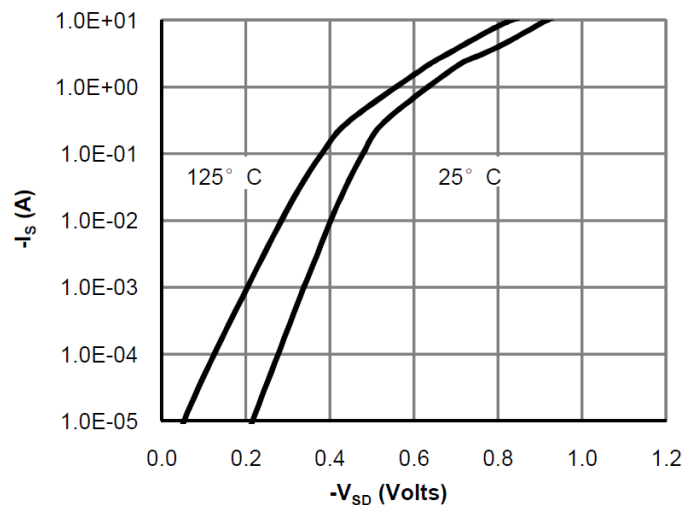
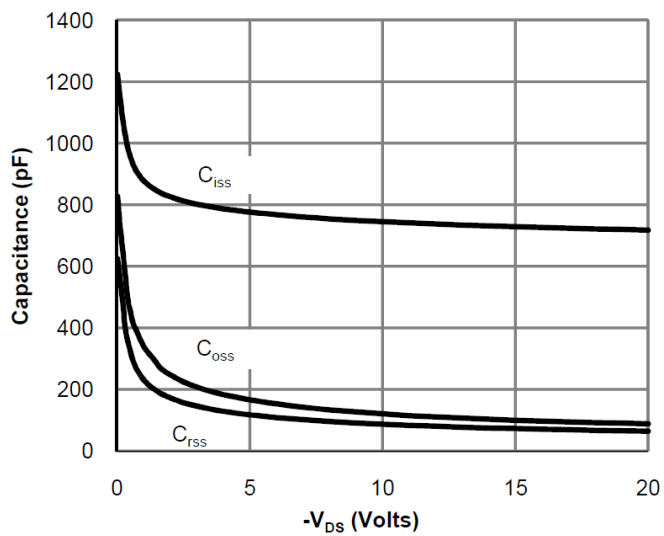


Figure 6: Body-Diode Characteristics

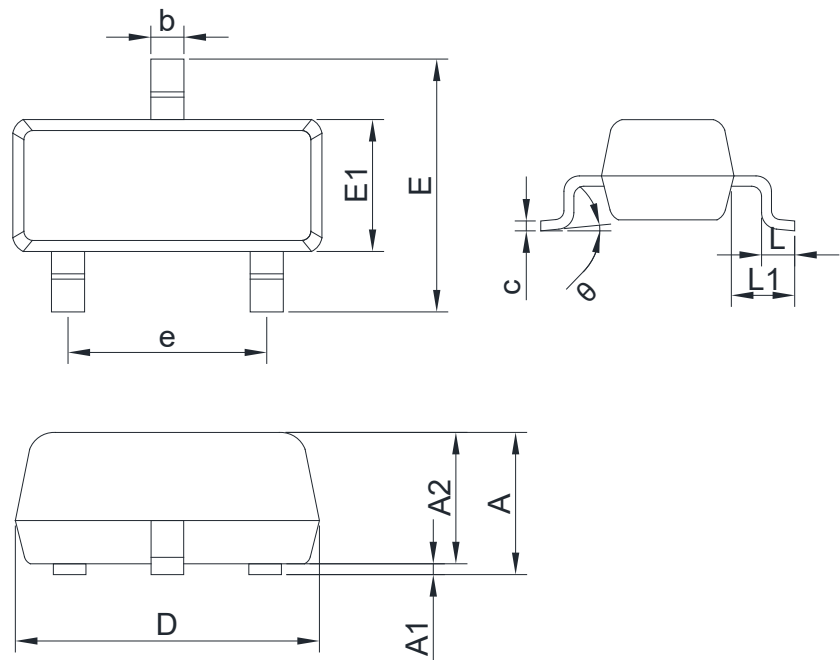
**Figure 7: Capacitance Characteristics**

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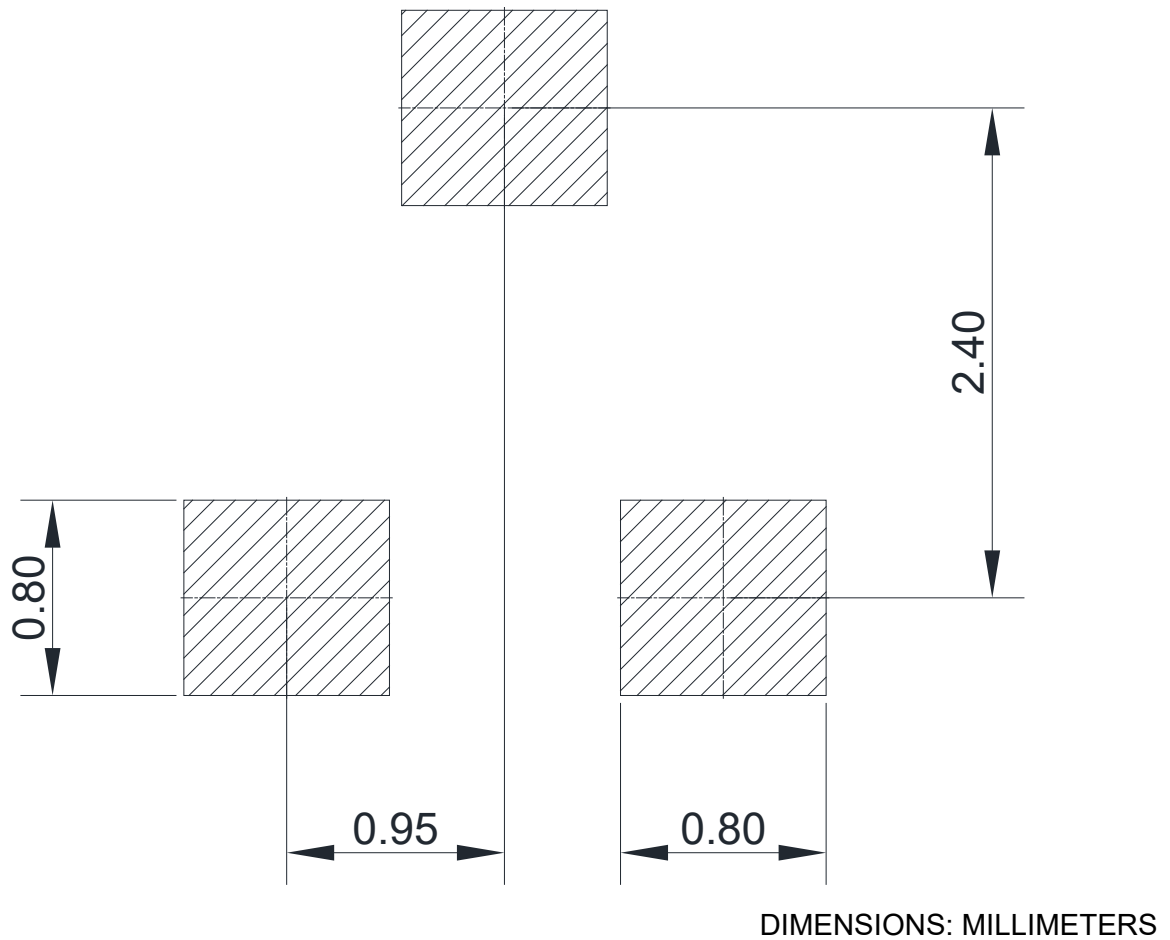
8. Dimension (SOT-23)

POD(Z)



COMMON DIMENSIONS CUNITS MEASURE=MILLIMETER					
SYMBOL	MIN	MAX	SYMBOL	MIN	MAX
A	0.90	1.20	E	2.25	2.55
A1	0.00	0.10	E1	1.20	1.40
A2	0.90	1.10	e	1.80	2.00
b	0.30	0.50	L	0.30	0.50
c	0.07	0.18	L1	0.475	0.625
D	2.80	3.04	θ	0°	8°

9. Recommended Soldering Footprint



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